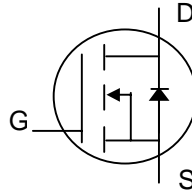


**N-CHANNEL ENHANCEMENT-MODE POWER MOSFET**

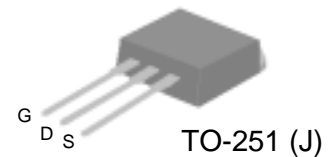
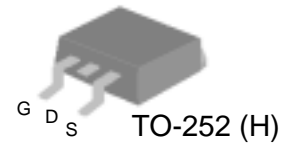
Dynamic dv/dt rating  
 Repetitive-avalanche rated  
 Fast switching  
 Simple drive requirement



$BV_{DSS}$  600V  
 $R_{DS(ON)}$  8 $\Omega$   
 $I_D$  1.6A

**Description**

The SSM01N60H is supplied in the industry-standard TO-252 package, which is widely preferred for commercial and industrial surface mount applications, and is well suited for AC/DC converters. The through-hole version (SSM01N60J) is available for low-footprint applications.


**Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	600	V
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$I_D @ T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	1.6	A
$I_D @ T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	1	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	6	A
$P_D @ T_C=25^\circ\text{C}$	Total Power Dissipation	39	W
	Linear Derating Factor	0.31	W/ $^\circ\text{C}$
$E_{AS}$	Single Pulse Avalanche Energy <sup>2</sup>	13	mJ
$I_{AR}$	Avalanche Current	1.6	A
$E_{AR}$	Repetitive Avalanche Energy	0.5	mJ
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

**Thermal Data**

Symbol	Parameter	Value	Unit
Rthj-c	Thermal Resistance Junction-case	Max. 3.2	$^\circ\text{C}/\text{W}$
Rthj-a	Thermal Resistance Junction-ambient	Max. 110	$^\circ\text{C}/\text{W}$

**Electrical Characteristics @  $T_j=25^{\circ}\text{C}$  (unless otherwise specified)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	600	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to $25^{\circ}\text{C}$ , $I_D=1\text{mA}$	-	0.6	-	$\text{V}/^{\circ}\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=0.8A$	-	7.2	8	$\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	-	4	V
$g_{fs}$	Forward Transconductance	$V_{DS}=10V, I_D=0.8A$	-	0.8	-	S
$I_{DSS}$	Drain-Source Leakage Current ( $T_j=25^{\circ}\text{C}$ )	$V_{DS}=600V, V_{GS}=0V$	-	-	10	$\mu A$
	Drain-Source Leakage Current ( $T_j=150^{\circ}\text{C}$ )	$V_{DS}=480V, V_{GS}=0V$	-	-	100	$\mu A$
$I_{GSS}$	Gate-Source Leakage	$V_{GS}=\pm 30V$	-	-	$\pm 100$	nA
$Q_g$	Total Gate Charge <sup>3</sup>	$I_D=1.6A$	-	7.7	-	nC
$Q_{gs}$	Gate-Source Charge	$V_{DS}=480V$	-	1.5	-	nC
$Q_{gd}$	Gate-Drain ("Miller") Charge	$V_{GS}=10V$	-	2.6	-	nC
$t_{d(on)}$	Turn-on Delay Time <sup>3</sup>	$V_{DD}=300V$	-	8	-	ns
$t_r$	Rise Time	$I_D=1.6A$	-	5	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=10\Omega, V_{GS}=10V$	-	14	-	ns
$t_f$	Fall Time	$R_D=187.5\Omega$	-	7	-	ns
$C_{iss}$	Input Capacitance	$V_{GS}=0V$	-	286	-	pF
$C_{oss}$	Output Capacitance	$V_{DS}=25V$	-	25	-	pF
$C_{rss}$	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	6	-	pF

**Source-Drain Diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$I_S$	Continuous Source Current ( Body Diode )	$V_D=V_G=0V, V_S=1.5V$	-	-	1.6	A
$I_{SM}$	Pulsed Source Current ( Body Diode ) <sup>1</sup>		-	-	6	A
$V_{SD}$	Forward On Voltage <sup>3</sup>	$T_j=25^{\circ}\text{C}, I_S=1.6A, V_{GS}=0V$	-	-	1.5	V

**Notes:**

1. Pulse width limited by safe operating area.
2. Starting  $T_j=25^{\circ}\text{C}$ ,  $V_{DD}=50V$ ,  $L=10\text{mH}$ ,  $R_G=25\Omega$ ,  $I_{AS}=1.6A$ .
3. Pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$ .

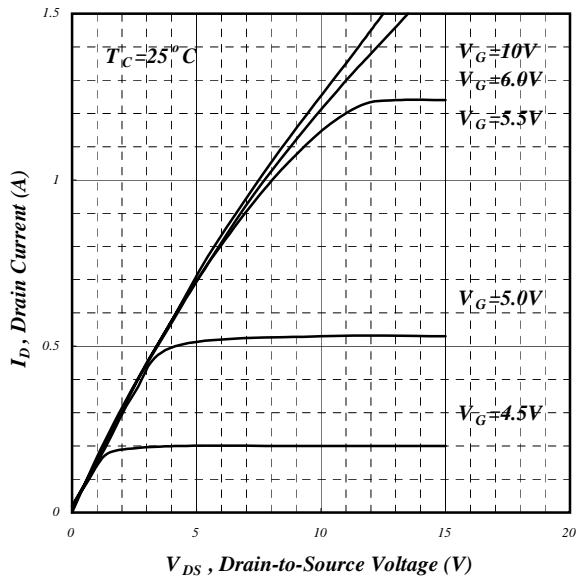


Fig 1. Typical Output Characteristics

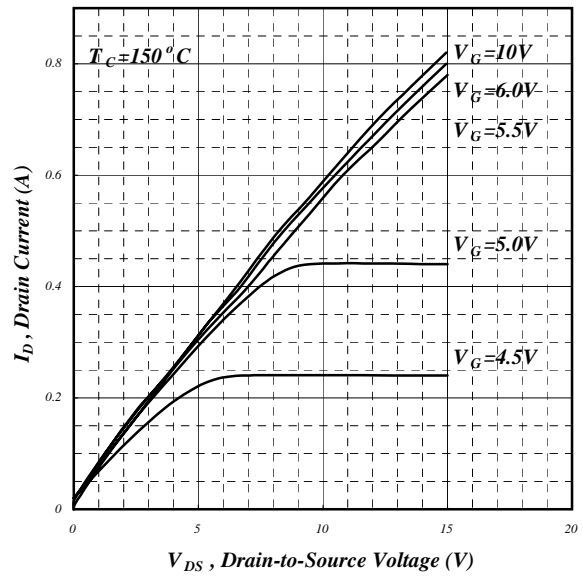


Fig 2. Typical Output Characteristics

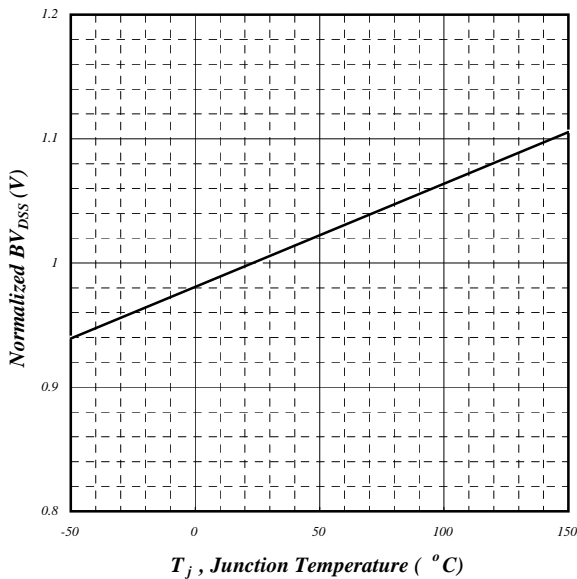


Fig 3. Normalized  $BV_{DSS}$  vs. Junction Temperature

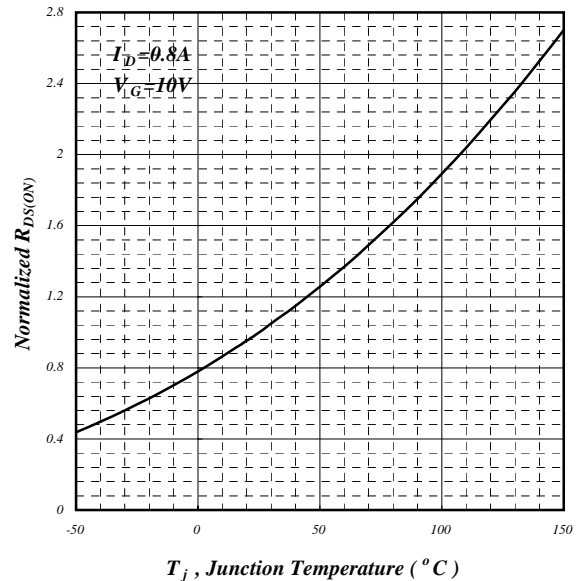


Fig 4. Normalized On-Resistance vs. Junction Temperature

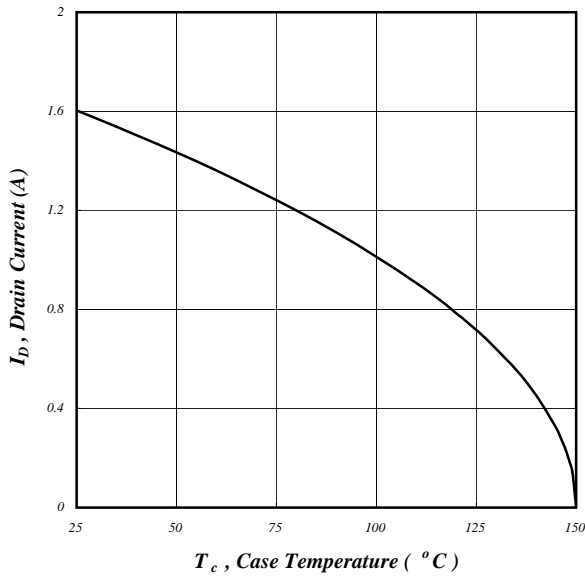


Fig 5. Maximum Drain Current vs. Case Temperature

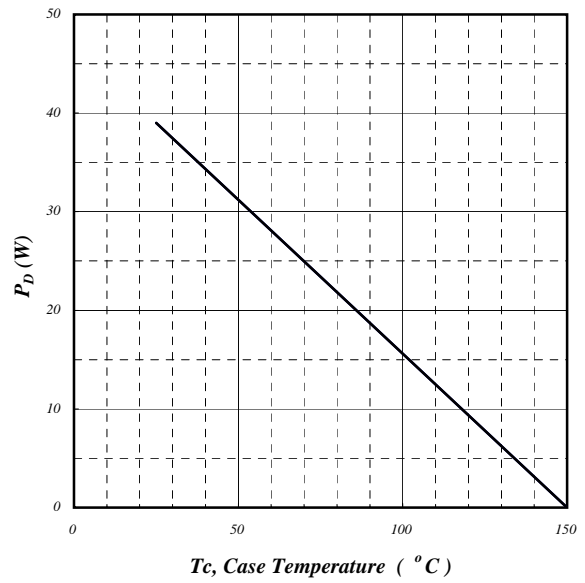


Fig 6. Typical Power Dissipation

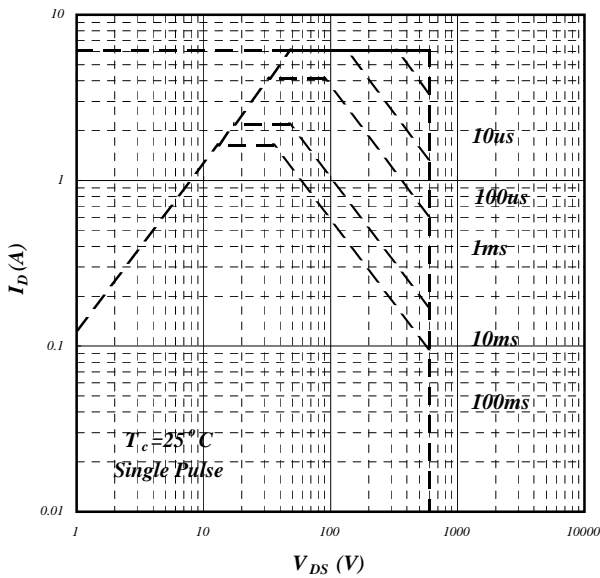


Fig 7. Maximum Safe Operating Area

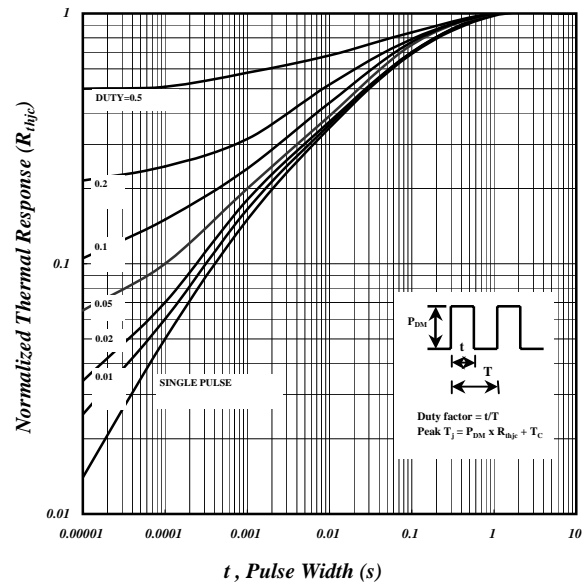


Fig 8. Effective Transient Thermal Impedance

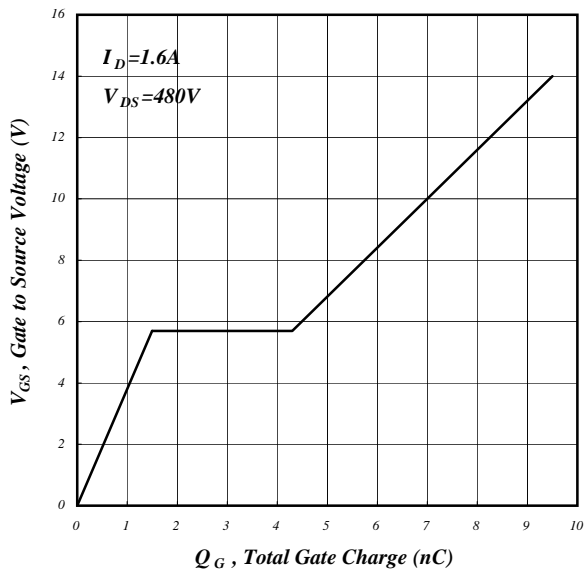


Fig 9. Gate Charge Characteristics

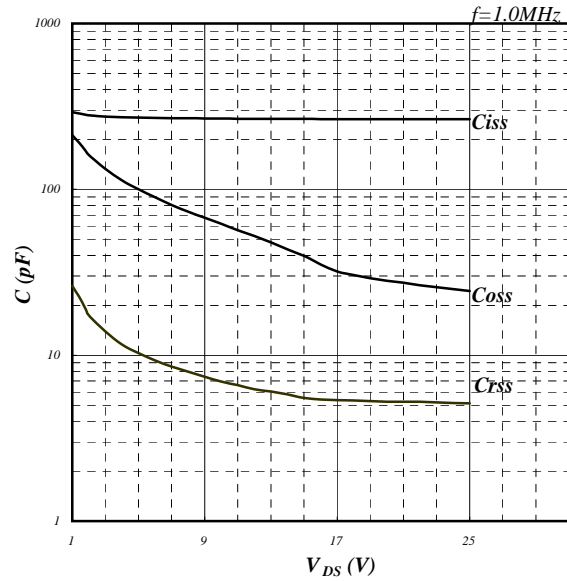


Fig 10. Typical Capacitance Characteristics

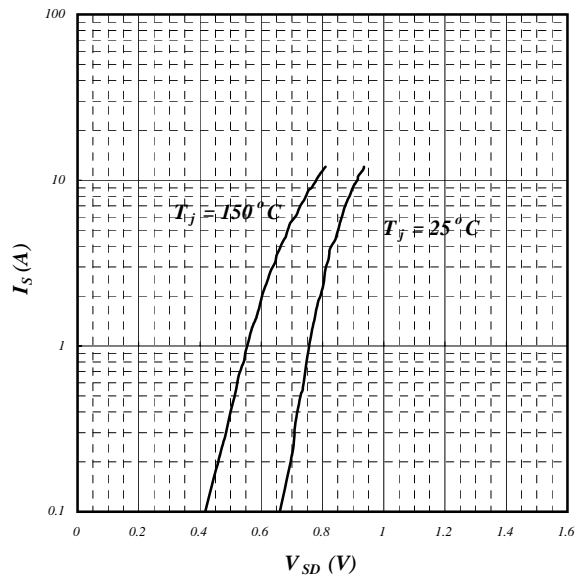


Fig 11. Forward Characteristic of Reverse Diode

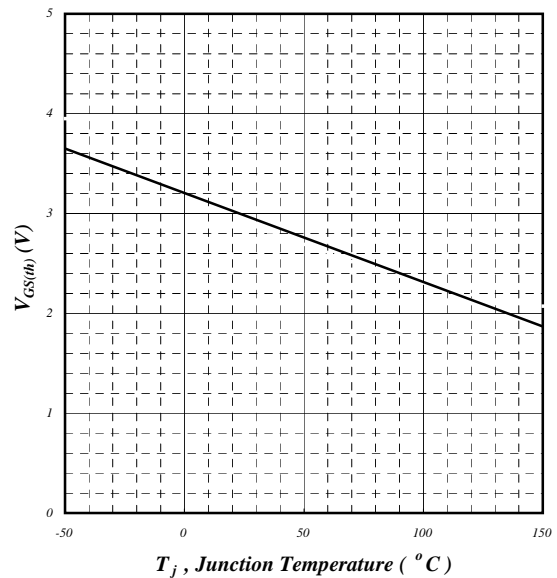


Fig 12. Gate Threshold Voltage vs. Junction Temperature

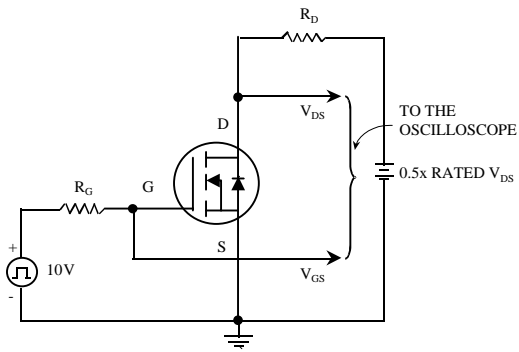


Fig 13. Switching Time Circuit

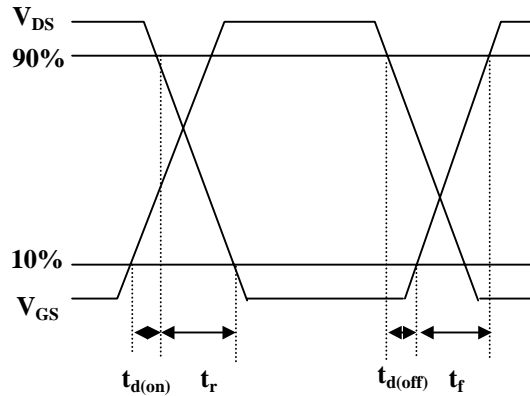


Fig 14. Switching Time Waveform

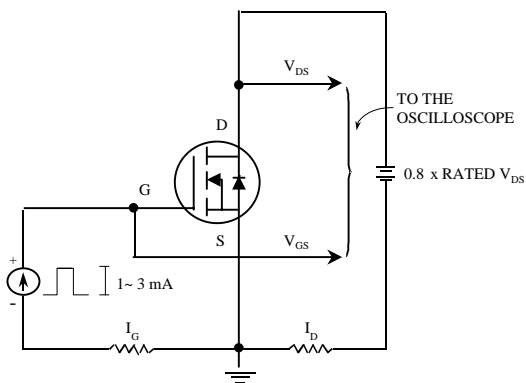


Fig 15. Gate Charge Circuit

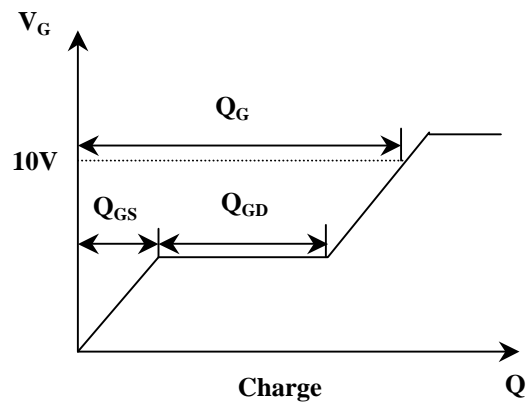


Fig 16. Gate Charge Waveform

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